

## 6/8inch General PVD System

### Model: SA-Polaris BM620

SA-Polaris BM620 is an automated 6/8-inch backside metallization PVD platform optimized for SiC power semiconductors. It deposits Ti, Ni, NiV and Ag for wafer rear-side metallization, precisely controlling film thickness and sheet resistance with uniformity less than 3%. Featuring compact cluster layout and robust warpage control, it achieves reliable mass production for power device back-metal processes with low particle contamination.



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SA-Polaris BM620

#### Feature

- Strict sheet resistance
- More stable
- Mass production
- Excellent warpage control capability

#### Application

- Si/SiC Power
- Ohmic Contact
- Barrier Layer
- Planarization

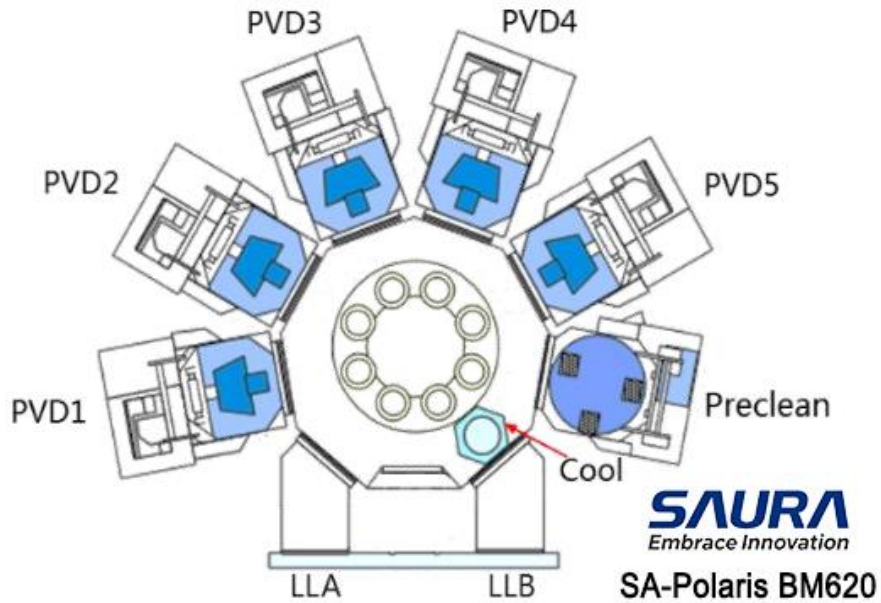
#### Specifications:

##### BSM

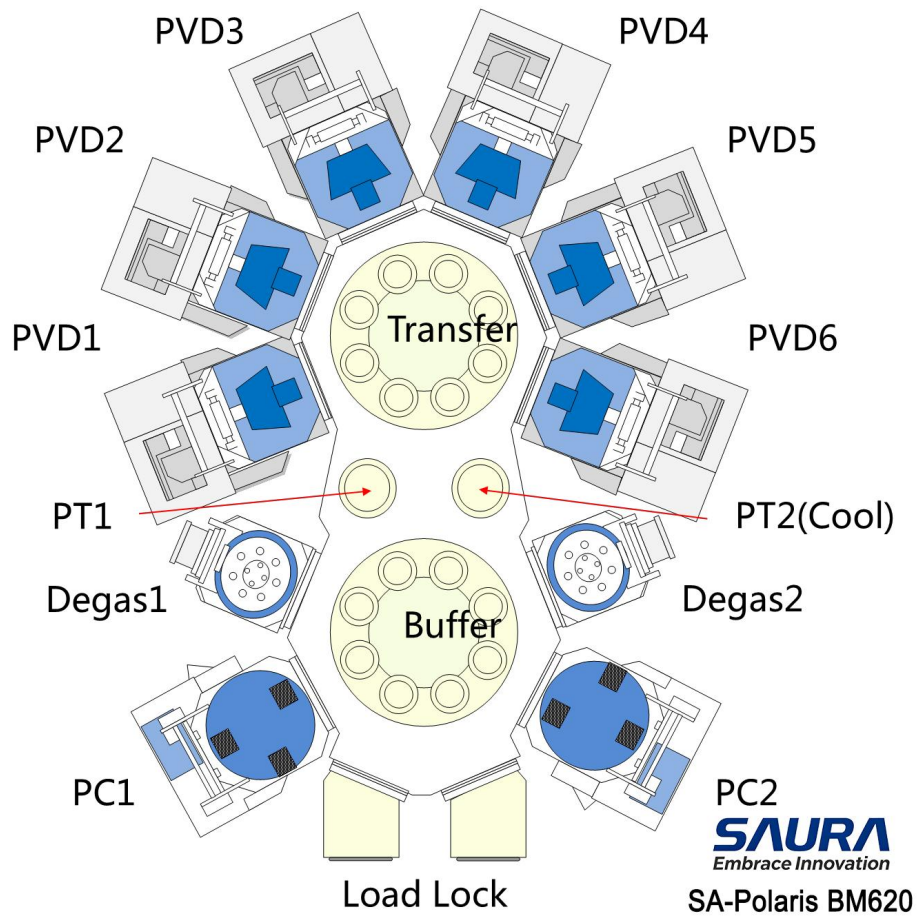
| Parameter       | Ni                                  | Ti           | Ag           |
|-----------------|-------------------------------------|--------------|--------------|
| Wafer Size      | 6/8inch                             |              |              |
| THK mean(A)     | 1500±75                             | 2000±100     | 10K±500      |
| Rs Mean(Ω/□)    | 0.6±0.1                             | 2.9±0.3      | 0.021±0.005  |
| Rs U%(WIW,%,16) | < 3@EE3                             | < 3@EE3      | < 3@EE3      |
| Infilm Particle | < 30ea@0.3μm                        | < 30ea@0.3μm | < 30ea@0.3μm |
| W×L×H           | 3200×2700×2200 mm/3100×4400×2200 mm |              |              |

**Principle:**

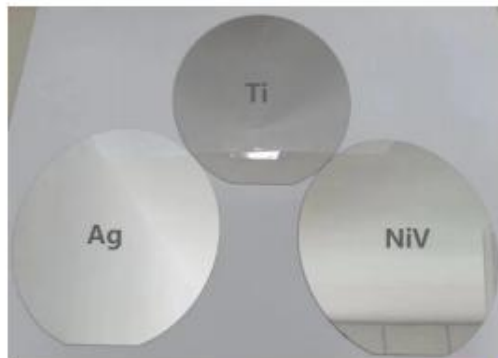
3200×2700×2200 mm



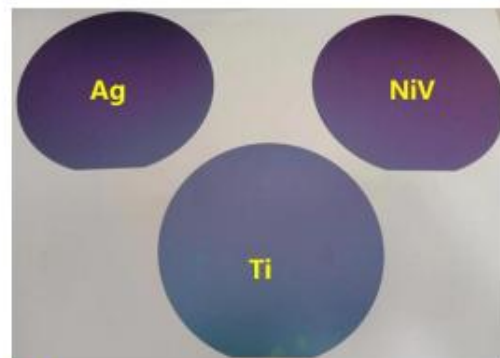
3100×4400×2200 mm



## Applications:

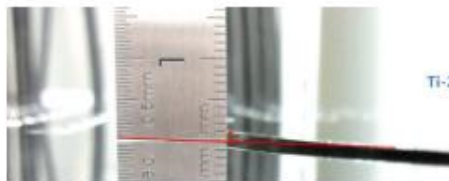


Film side



Wafer Back side

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Before BSM, warpage=1mm

Ti-2KA ; Ni-1.5KA ; Ag-1um



After BSM, warpage=1.2mm